



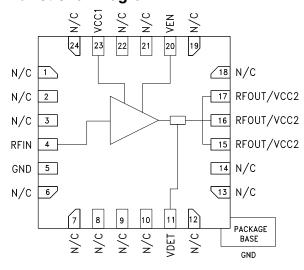
## GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz

### Typical Applications

The HMC921LP4E is ideal for:

- Cellular/3G & WiMAX/LTE/4G
- Fixed Wireless & WLAN
- CATV, Cable Modem & DBS
- Microwave Radio & Test Equipment
- IF & RF Applications

### **Functional Diagram**



#### **Features**

High Output IP3: +48 dBm High Output P1dB: +33 dBm High Gain: 16 dB @ 900 MHz

Single Supply: +5V

32% PAE @ +33 dBm Pout

Adjustable Bias Current

24 Lead 4x4 mm SMT Package: 16 mm<sup>2</sup>

### General Description

The HMC921LP4E is a high linearity GaAs HBT MMIC 2 watt power amplifier operating from 0.4 to 2.7 GHz and is housed in a RoHS compliant 4x4 mm QFN leadless package. The HMC921LP4E utilizes a minimum number of external components and operates from a single +5V supply. This versatile power amplifier can be biased for both low quiescent current and high quiescent current modes by adjusting a single external resistor.

### Electrical Specifications, T<sub>4</sub> = +25°C, Vcc1 = Vcc2 = VEN = +5V [1]

Development					400 mA (R1 = 270 Ω)												
Parameter		Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Units
Frequency Range		3	50 - 50	0	80	00 - 100	00	18	00 - 20	00	20	00 - 22	200	25	00 - 28	00	MHz
Gain		17	19		14	16		9	11		9.5	10.5		8	9		dB
Gain Variation Over Temperat	ure		0.01			0.01			0.01			0.01			0.01		dB / °C
Input Return Loss		9	12		10	15		5	10		8	12		6	11		dB
Output Return Loss		6	10		5	9		8	9		6	7		9	10		dB
Output Power for 1dB Compression (P1dB)		32.5	34		30.5	32		31	32.5		32	32.5		33	33.3		dBm
Saturated Output Power (Psa	t)		35			34			34			34			34.5		dBm
Output Third Order Intercept (IP3)			47			44			43			43			45		dBm
Noise Figure			12.9			9			8.5			6.9			6.5		dB
lo	en cc1 cc2		8 12 400			8 12 400			8 12 400			8 12 400			8 12 400		mA mA mA

[1] Specifications and data reflect HMC921LP4E measured using the respective application circuits for each designated frequency band found herein. Contact the HMC Applications Group for assistance in optimizing performance for your application.

# **HMC921\* PRODUCT PAGE QUICK LINKS**

Last Content Update: 02/23/2017

## COMPARABLE PARTS 🖵

View a parametric search of comparable parts.

### **EVALUATION KITS**

- HMC921LP4E Evaluation Board
- Two Channels, 2400MHz TDD Application

### **DOCUMENTATION** $\Box$

### **Data Sheet**

• HMC921 Data Sheet

### REFERENCE MATERIALS $\Box$

#### **Quality Documentation**

- Package/Assembly Qualification Test Report: LP4, LP4B, LP4C, LP4K (QTR: 2013-00487 REV: 04)
- Semiconductor Qualification Test Report: GaAs HBT-D (QTR: 2013-00252)

# DESIGN RESOURCES 🖵

- HMC921 Material Declaration
- PCN-PDN Information
- · Quality And Reliability
- Symbols and Footprints

### **DISCUSSIONS**

View all HMC921 EngineerZone Discussions.

### SAMPLE AND BUY 🖵

Visit the product page to see pricing options.

### **TECHNICAL SUPPORT**

Submit a technical question or find your regional support number.

### DOCUMENT FEEDBACK 🖳

Submit feedback for this data sheet.





# GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz

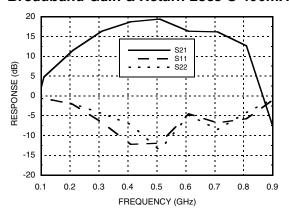
### Electrical Specifications, $T_A = +25^{\circ}\text{C}$ , $Vcc1 = Vcc2 = VEN = +5V^{[1]}$

	700 mA (R1 = 130 Ω)															
Parameter	Min.	Min. Typ. N		Min.	Тур.	Max.	Units									
Frequency Range	3	50 - 50	0	80	00 - 10	00	18	00 - 20	00	20	00 - 22	00	26	00 - 28	00	MHz
Gain	19	19.5		14	16		9	11		10.3	10.8		8	9		dB
Gain Variation Over Temperature		001			0.01			0.01			0.01			0.01		dB / °C
Input Return Loss	9	12		11	15		6	10		9	13		6	12		dB
Output Return Loss	6	10		6	9		8	9		6	7.5		9	10		dB
Output Power for 1dB Compression (P1dB)	33	34.5		31	32.5		31.5	33		32.8	33.5		33	34		dBm
Saturated Output Power (Psat)		35			34			34			34.5			35		dBm
Output Third Order Intercept (IP3)		43			45			46			47			47		dBm
Noise Figure		14			9			8.5			8			8		dB
Supply Current (Icq) Ien Icc1 Icc2		13 14 700			13 14 700			13 14 700			13 14 700			13 14 700		mA mA mA

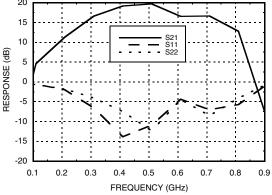
<sup>[1]</sup> Specifications and data reflect HMC921LP4E measured using the respective application circuits for each designated frequency band found herein. Contact the HMC Applications Group for assistance in optimizing performance for your application.

#### 450 MHz Tune

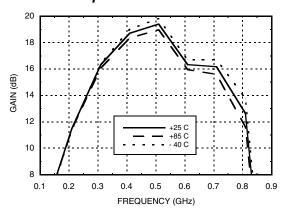
### Broadband Gain & Return Loss @ 400mA



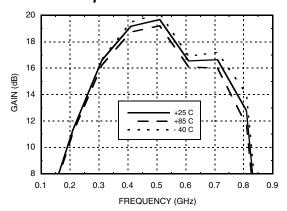
# Broadband Gain & Return Loss @ 700mA



### Gain vs. Temperature @ 400mA



### Gain vs. Temperature @ 700mA



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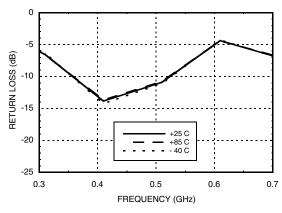




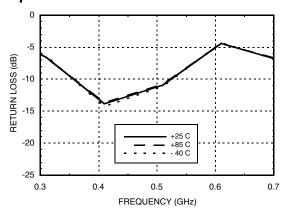
### GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz

### 450 MHz Tune

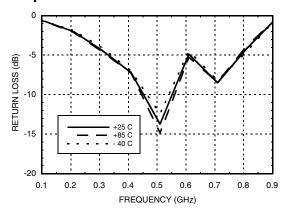
### Input Return Loss @ 400 mA



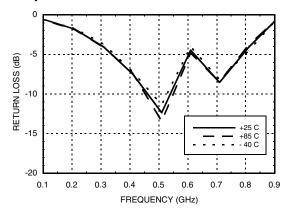
### Input Return Loss @ 700 mA



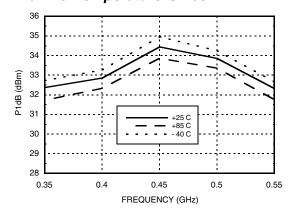
### Output return Loss @ 400 mA



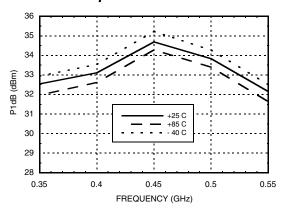
### Output return Loss @ 700 mA



### P1dB vs. Temperature @ 400 mA



### P1dB vs. Temperature @ 700 mA



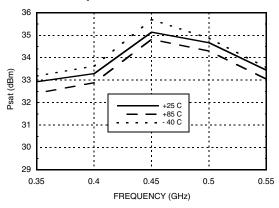




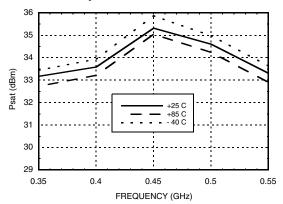
### GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz

### 450 MHz Tune

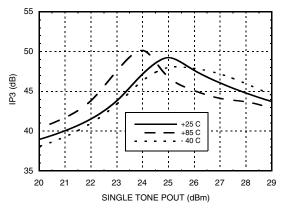
### Psat vs. Temperature @ 400mA



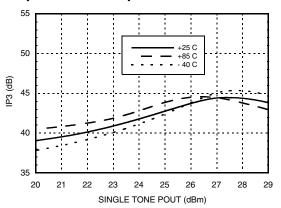
### Psat vs. Temperature @ 700mA



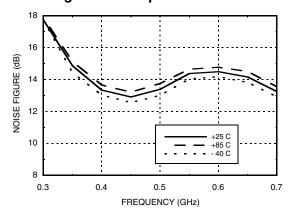
### Output IP3 vs. Output Power @ 400mA



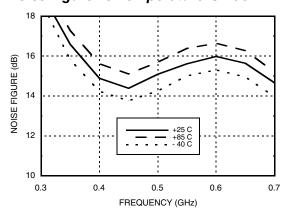
### Output IP3 vs. Output Power @ 700mA



### Noise Figure vs. Temperature @ 400mA



### Noise Figure vs. Temperature @ 700mA



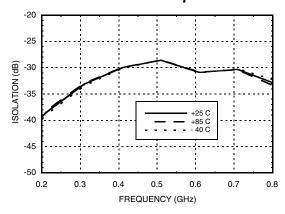




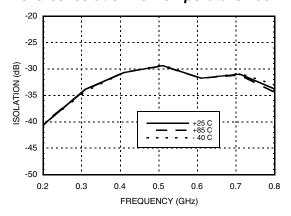
## GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz

450 MHz Tune

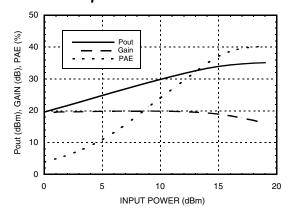
### Reverse Isolation vs. Temperature 400mA



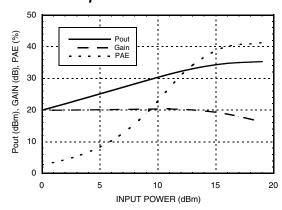
### Reverse Isolation vs. Temperature 700mA



### Power Compression @ 400mA



### Power Compression @ 700mA



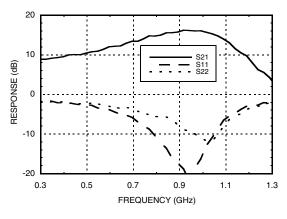




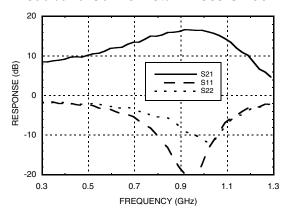
# GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz

### 900 MHz Tune

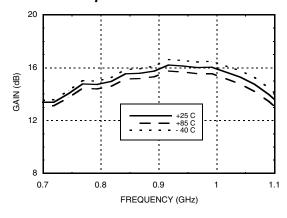
### Broadband Gain & Return Loss @ 400 mA



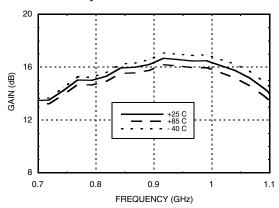
#### Broadband Gain & Return Loss @ 700 mA



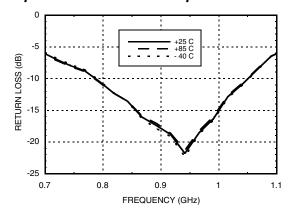
### Gain vs. Temperature @ 400 mA



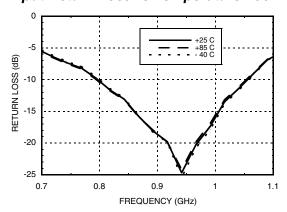
Gain vs. Temperature @ 700 mA



### Input Return Loss vs. Temperature 400mA



### Input Return Loss vs. Temperature 700mA

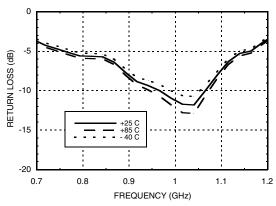




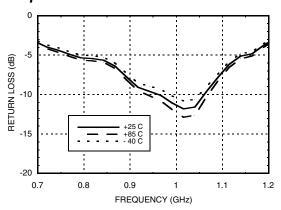


# GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz 900 MHz Tune

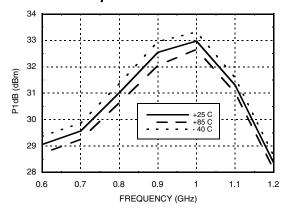
### Output Return Loss @ 400mA



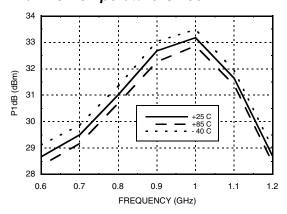
### Output Return Loss @ 700mA



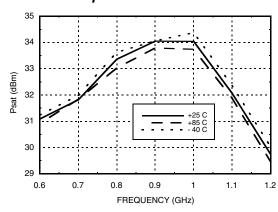
### P1dB vs. Temperature @ 400 mA



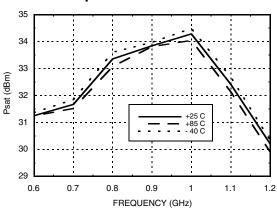
P1dB vs. Temperature @ 700 mA



### Psat vs. Temperature @ 400 mA



Psat vs. Temperature @ 700 mA

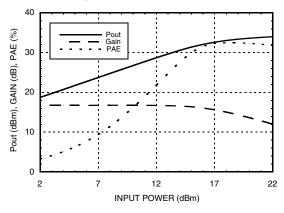




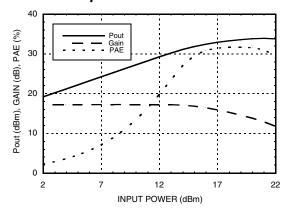


# GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz 900 MHz Tune

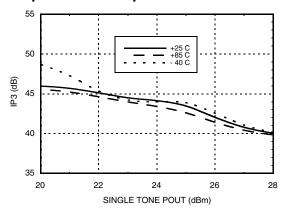
### Power Compression @ 400 mA



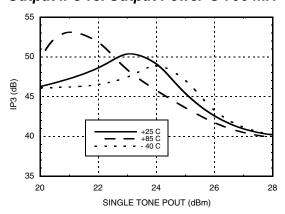
### Power Compression @ 700 mA



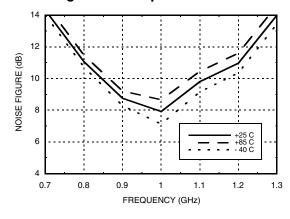
### Output IP3 vs. Output Power @ 400 mA



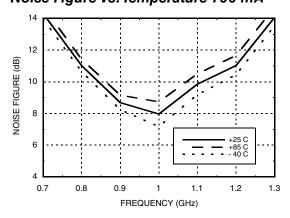
### Output IP3 vs. Output Power @ 700 mA



### Noise Figure vs. Temperature 400 mA



### Noise Figure vs. Temperature 700 mA



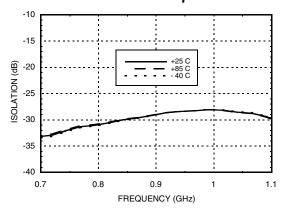




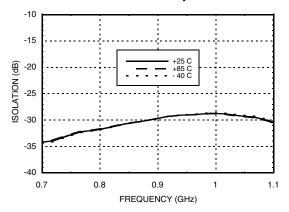
# GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz

900 MHz Tune

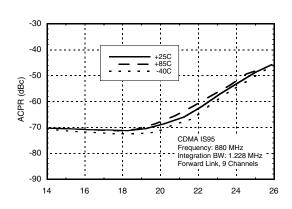
### Reverse Isolation vs. Temperature 400mA



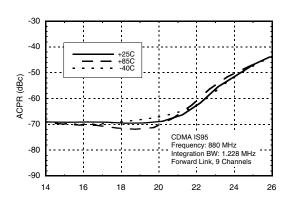
### Reverse Isolation vs. Temperature 700mA



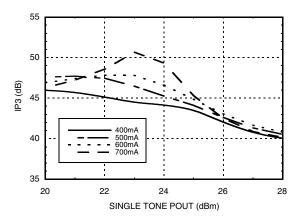
### ACPR vs. Temperature @ 880 MHz CDMA 2000, 9 Channels Forward, 400 mA



ACPR vs. Temperature @ 880 MHz CDMA 2000, 9 Channels Forward, 700 mA



### Output IP3 vs. Bias Current



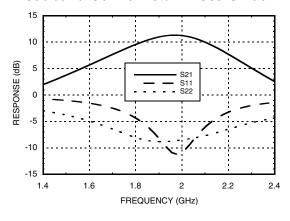




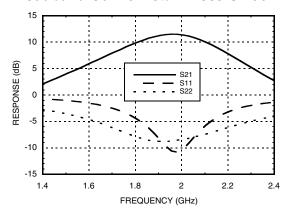
# GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz

### 1900 MHz Tune

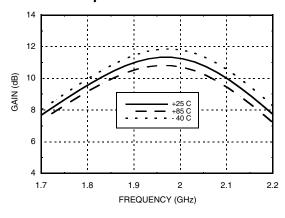
#### Broadband Gain & Return Loss @ 400 mA



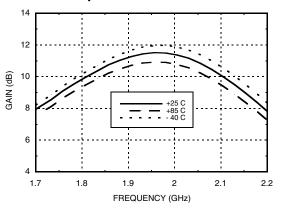
#### Broadband Gain & Return Loss @ 700 mA



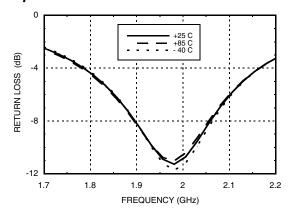
### Gain vs. Temperature @ 400 mA



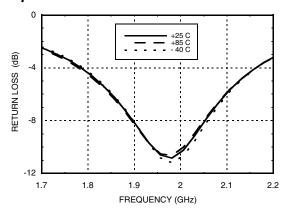
Gain vs. Temperature @ 700 mA



### Input Return Loss @ 400 mA



### Input Return Loss @ 700 mA



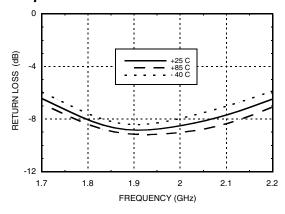




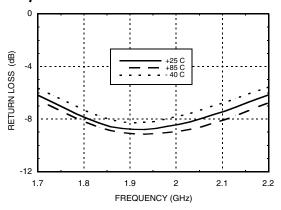
# GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz

#### 1900 MHz Tune

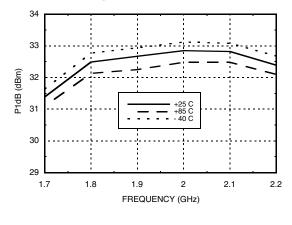
### Output Return Loss @ 400 mA



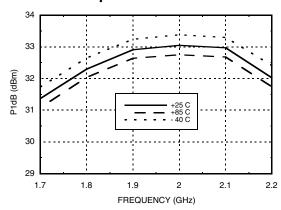
### Output Return Loss @ 700 mA



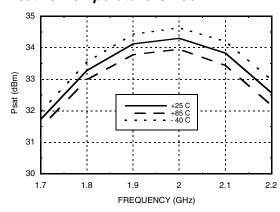
### P1dB vs. Temperature @ 400 mA



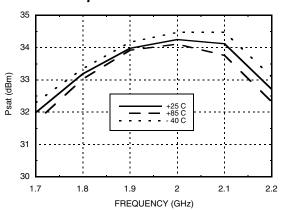
P1dB vs. Temperature @ 700 mA



### Psat vs. Temperature @ 400 mA



### Psat vs. Temperature @ 700 mA



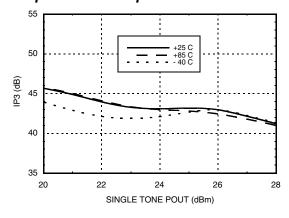




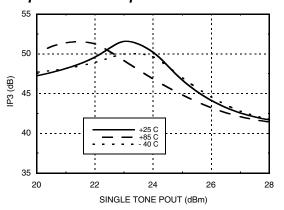
# GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz

### 1900 MHz Tune

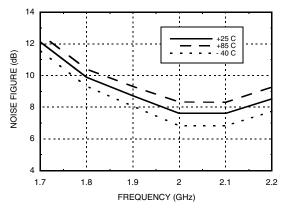
### Output IP3 vs. Output Power @ 400 mA



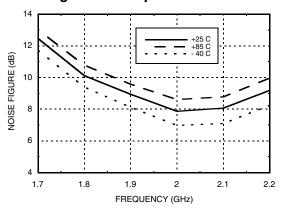
### Output IP3 vs. Output Power @ 700 mA



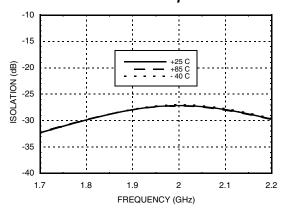
### Noise Figure vs. Temperature @ 400 mA



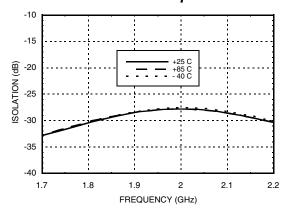
### Noise Figure vs. Temperature @ 700 mA



### Reverse Isolation vs. Temperature 400 mA



### Reverse Isolation vs. Temperature 700 mA

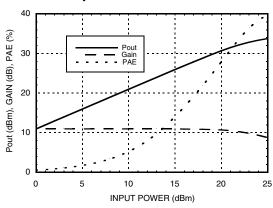


# ANALOG DEVICES

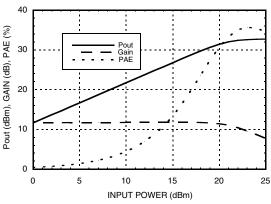
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# GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz 1900 MHz Tune

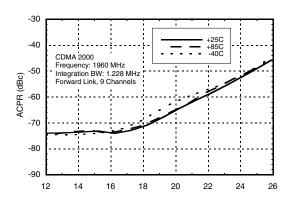
### Power Compression @ 400 mA



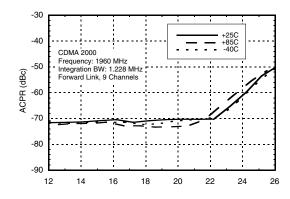
# Power Compression @ 700 mA



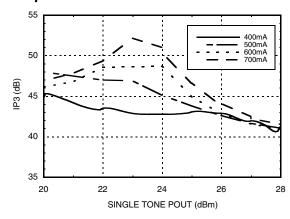
# ACPR vs. Temperature @ 1960 MHz CDMA 2000, 9 Channels Forward, 400 mA



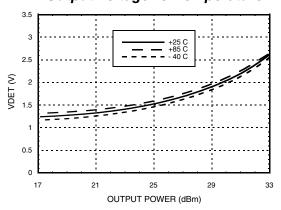
ACPR vs. Temperature @ 1960 MHz CDMA 2000, 9 Channels Forward, 700 mA



### Output IP3 vs. Bias Current



### **VDET Output Voltage vs. Temperature**

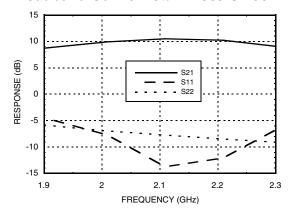




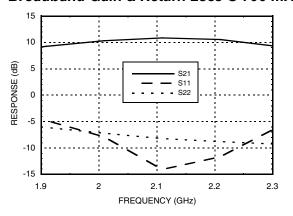


# GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz 2150 MHz Tune

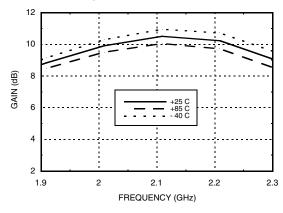
#### Broadband Gain & Return Loss @ 400 mA



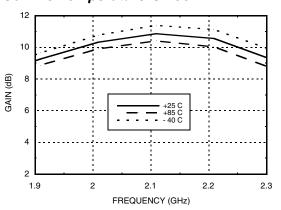
### Broadband Gain & Return Loss @ 700 mA



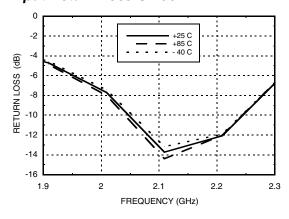
### Gain vs. Temperature @ 400 mA



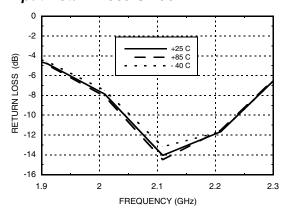
Gain vs. Temperature @ 700 mA



### Input Return Loss @ 400 mA



### Input Return Loss @ 700 mA



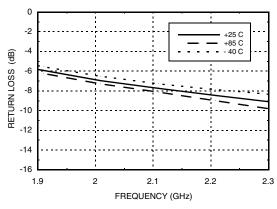




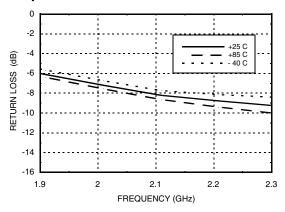
# GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz

#### 2150 MHz Tune

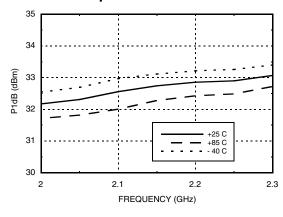
### Output Return Loss @ 400 mA



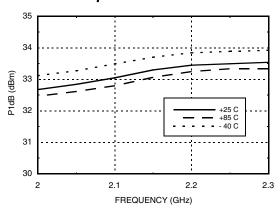
### Output Return Loss @ 700 mA



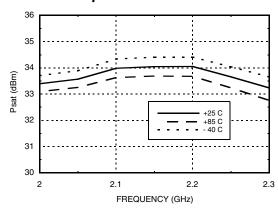
### P1dB vs. Temperature @ 400 mA



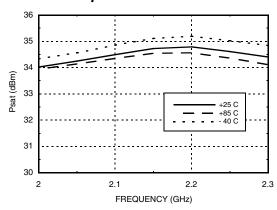
P1dB vs. Temperature @ 700 mA



### Psat vs. Temperature @ 400 mA



Psat vs. Temperature @ 700 mA

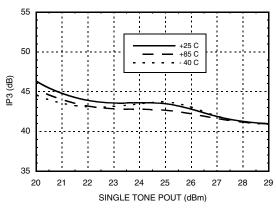




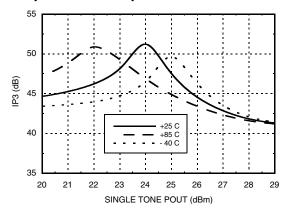


# GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz 2150 MHz Tune

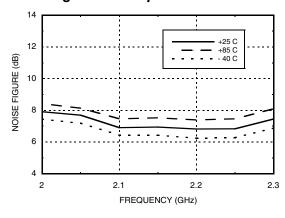
### Output IP3 vs Output Power @ 400 mA



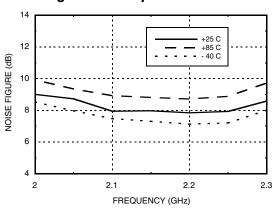
### Output IP3 vs Output Power @ 700 mA



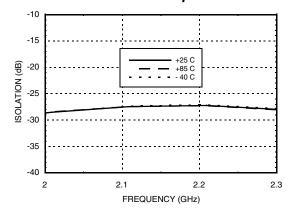
### Noise Figure vs. Temperature @ 400 mA



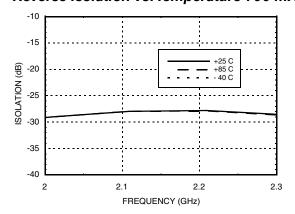
### Noise Figure vs. Temperature @ 700 mA



### Reverse Isolation vs. Temperature 400 mA



### Reverse Isolation vs. Temperature 700 mA

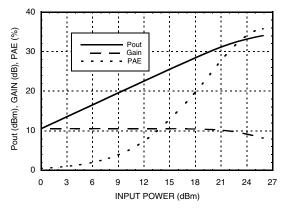




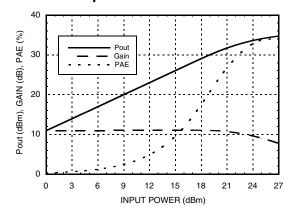


# GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz 2150 MHz Tune

### Power Compression @ 400 mA



### Power Compression @ 700 mA

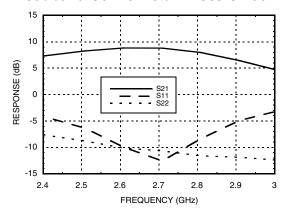




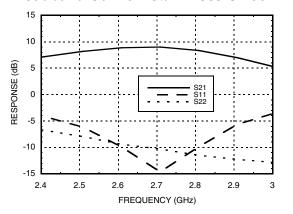


# GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz 2700 MHz Tune

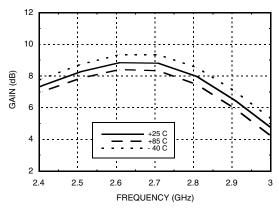
### Broadband Gain & Return Loss @ 400 mA



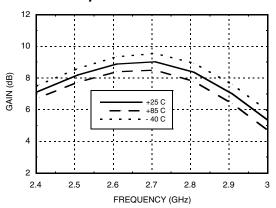
### Broadband Gain & Return Loss @ 700 mA



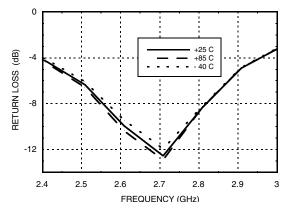
### Gain vs. Temperature @ 400 mA



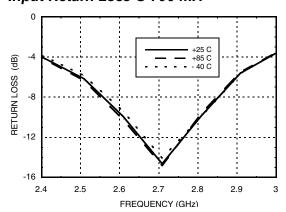
Gain vs. Temperature @ 700 mA



### Input Return Loss @ 400 mA



### Input Return Loss @ 700 mA



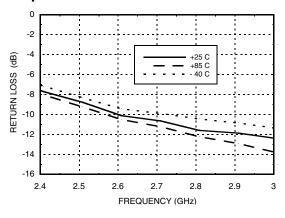




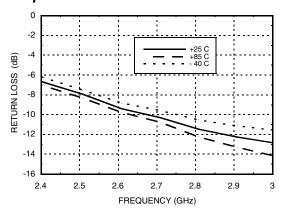
# GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz

#### 2700 MHz Tune

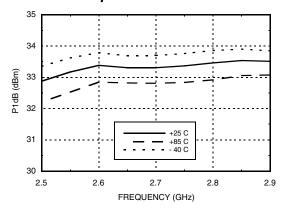
### Output Return Loss @ 400 mA



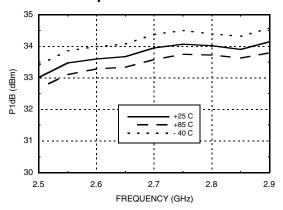
### Output Return Loss @ 700 mA



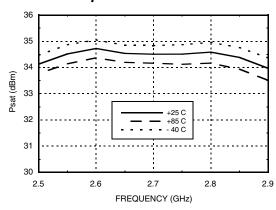
### P1dB vs. Temperature @ 400 mA



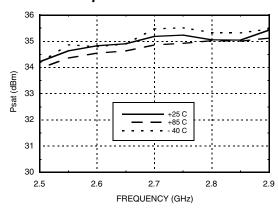
### P1dB vs. Temperature @ 700 mA



### Psat vs. Temperature @ 400 mA



### Psat vs. Temperature @ 700 mA

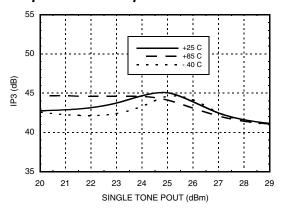




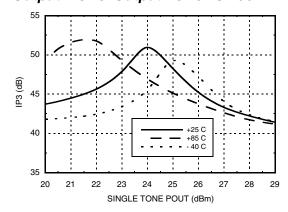


# GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz 2700 MHz Tune

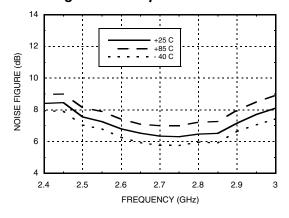
### Output IP3 vs. Output Power @ 400 mA



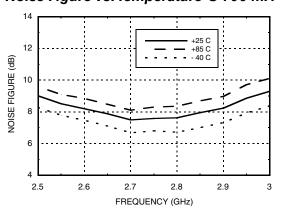
### Output IP3 vs. Output Power @ 700 mA



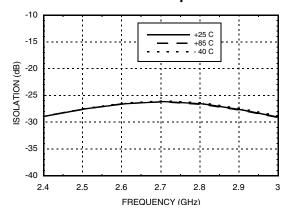
### Noise Figure vs. Temperature @ 400 mA



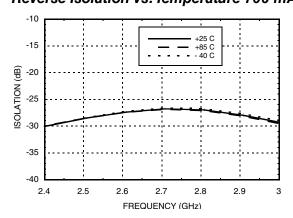
### Noise Figure vs. Temperature @ 700 mA



### Reverse Isolation vs. Temperature 400 mA



### Reverse Isolation vs. Temperature 700 mA

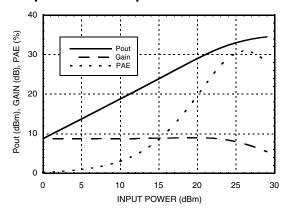




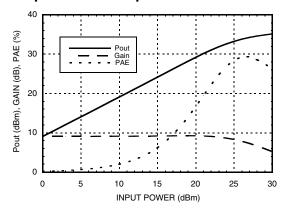


# GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz 2700 MHz Tune

### Output IP3 vs. Output Power @ 400 mA



### Output IP3 vs. Output Power @ 700 mA

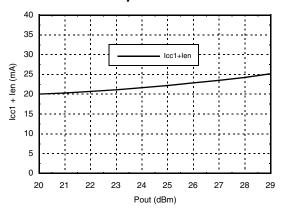




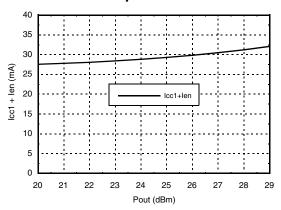


## GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz

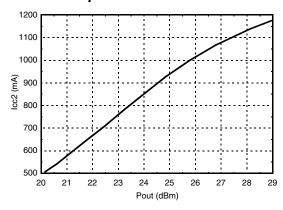
### Icc1 + IEN vs. Output Power @ 400 mA



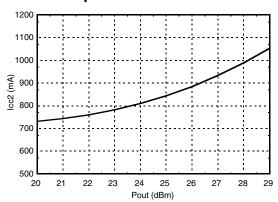
### Icc1 + IEN vs. Output Power @ 700 mA



### Icc2 vs. Output Power @ 400 mA



### Icc2 vs. Output Power @ 700 mA



### **Absolute Maximum Ratings**

Collector Bias Voltage (Vcc1, Vcc2)	+5.5V
RF Input Power (RFIN)	+21 dBm @ 900 MHz +26 dBm @ 1900 MHz
Junction Temperature	150 °C
Continuous Pdiss (T = 85 °C) (derate 67.9 mW/°C above 85 °C)	4.4 W
Thermal Resistance (junction to ground paddle)	14.72 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C
ESD Sensitivity (HBM)	Class 1C

# Recommended Bias Resistor Value Bias Current vs. R1, Ven = 5V

Vcc1 = Vcc2 (V)	R1 (Ohms)	len + lcc1 + lcc2 (mA)
	270	420
EV.	225	522
5V	175	625
	130	715

### Bias Current vs. R1, Ven = 0V

Vcc1 = Vcc2 (V)	R1 (Ohms)	len + lcc1 + lcc2 (mA)
	270	2.6
EV.	225	2.6
5V	175	2.6
	130	2.6

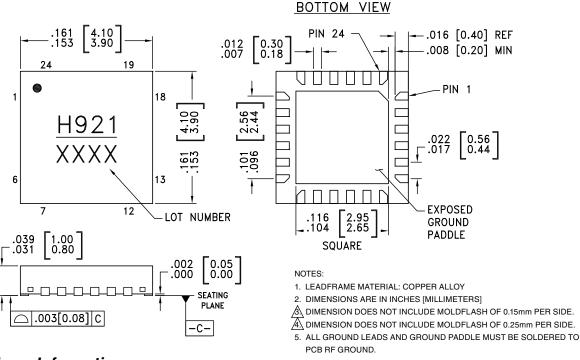






## GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz

### **Outline Drawing**



### Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking [1]
HMC921LP4E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 [2]	<u>H921</u> XXXX

<sup>[1] 4-</sup>Digit lot number XXXX

### **Pin Descriptions**

Pin Number	Function	Description	Interface Schematic
1 - 3, 6 - 10, 12 - 14, 18, 19, 21, 22, 24	N/C	The pins are not connected internally; however, all data shown herein was measured with these pins connected to RF/DC ground externally.	
4	RFIN	This pin is DC coupled. Off chip matching components are required. See Application Circuit herein.	RFIN O——— ORFOUT
15 - 17	RFOUT / Vcc2	RF output and DC Bias input for the amplifier. Off chip matching components are required. See Application Circuit herein.	
5	GND	These pins & package bottom must be connected to RF/DC ground.	GND
11	VDET	DC voltage output proportional to RFOUT signal.	
20	VEN	Power control pin. This voltage can be reduced or R1 resistor value increased to reduce quiescent current. For full power down, apply < 0.5V	
23	Vcc1	DC power supply pin for bias circuitry	

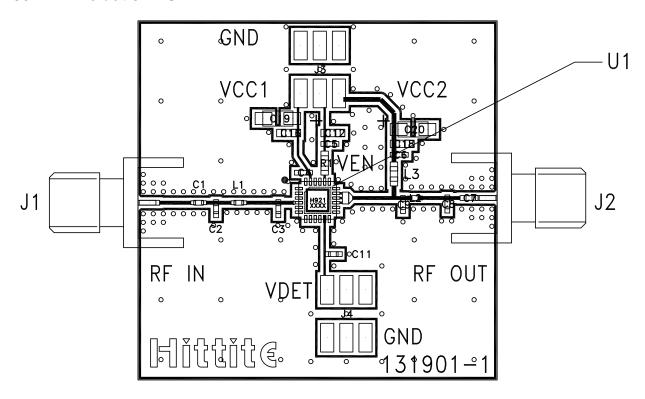
<sup>[2]</sup> Max peak reflow temperature of 260 °C





### GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz

#### 450 MHz Evaluation PCB



#### List of Materials for 450 MHz Evaluation PCB 131903 [1]

Item	Description
J1, J2	SMA Connector
J3, J4	DC Pin
C1, C9	30 pF Capacitor, 0402 Pkg.
C2	15 pF Capacitor, 0402 Pkg.
C3	27 pF Capacitor, 0402 Pkg.
C4 - C6, C11	100 pF Capacitor, 0402 Pkg.
C9, C20	2.2 uF Capacitor, Case A
C12, C16, C18	1000 pF Capacitor, 0402 Pkg.
R1	130 ohms Resistor, 0603 Pkg.
L1	3.6 nH Inductor, 0402 Pkg.
L2	4.7 nH Inductor, 0402 Pkg.
L3	150 nH Inductor, 0603 Pkg.
U1	HMC921LP4E Amplifier
PCB [2]	131901 Evaluation PCB

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350 or Arlon 25 FR

The circuit board used in this application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.

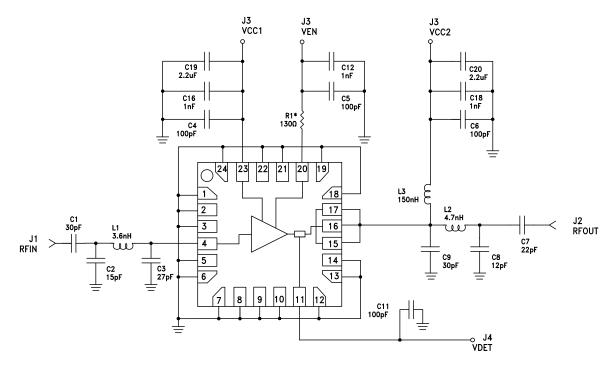




# GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz

### 450 MHz Application Circuit

This circuit was used to specify the performance for 350 - 500 MHz operation. Contact the HMC Applications Group for assistance in optimizing performance for your application.



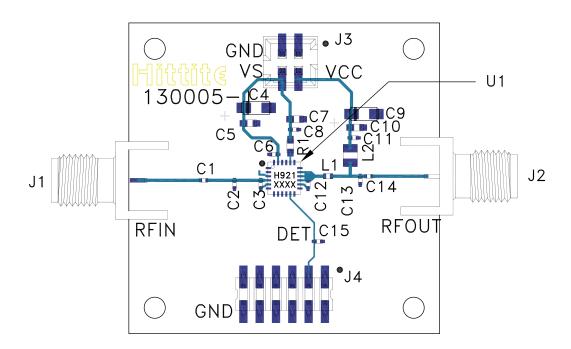
<sup>\*</sup> R1 = 130 Ohms for 700 mA bias, 270 Ohms for 400 mA bias.





## GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz

### 900 MHz Evaluation PCB



### List of Materials for 900 MHz Evaluation PCB 130007 [1]

Item	Description
J1 - J2	PCB Mount SMA Connector
J3 - J4	2 mm DC Header
C1	22 pF Capacitor, 0402 Pkg.
C2	7.5 pF Capacitor, 0402 Pkg.
C3	5.6 pF Capacitor, 0402 Pkg.
C4, C9	2.2 µF Capacitor, Tantalum
C5, C7, C10	1000 pF Capacitor, 0603 Pkg.
C6, C8, C11, C14, C15	100 pF Capacitor, 0402 Pkg.
C12, C13	8.2 pF Capacitor, 0402 Pkg.
L1	0.78 nH Inductor, 0402 Pkg.
L2	48 nH Inductor, 0402 Pkg.
R1	130 Ohms Resistor, 0603 Pkg.
U1	HMC921LP4E Linear Amplifier
PCB [2]	130005 Evaluation PCB

[1] Reference this number when ordering complete evaluation PCB  $\,$ 

[2] Circuit Board Material: Rogers 4350 or Arlon 25 FR

The circuit board used in this application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.

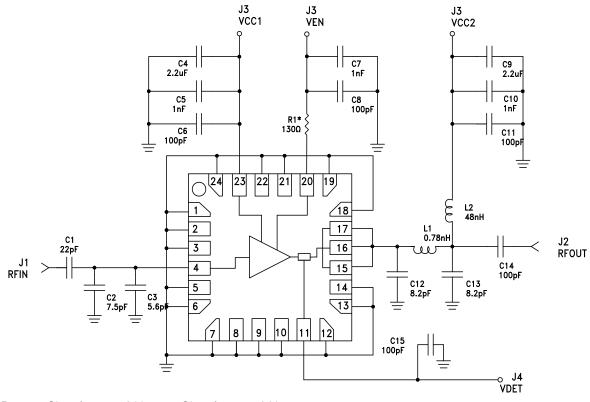




## GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz

### 900 MHz Application Circuit

This circuit was used to specify the performance for 800 - 1000 MHz operation. Contact the HMC Applications Group for assistance in optimizing performance for your application.



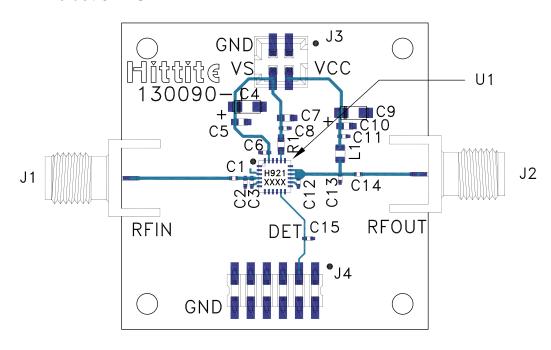
<sup>\*</sup> R1 = 130 Ohms for 700 mA bias, 270 Ohms for 400 mA bias.





## GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz

### 1900 MHz Evaluation PCB



### List of Materials for 1900 MHz Evaluation PCB 130008 [1]

Item	Description
J1 - J2	PCB Mount SMA Connector
J3 - J4	2 mm DC Header
C1	0.9 pF Capacitor, 0402 Pkg.
C2	0.9 pF Capacitor, 0402 Pkg.
C3	1.8 pF Capacitor, 0402 Pkg.
C4, C9	2.2 μF Capacitor, Tantalum
C5, C7, C10	1000 pF Capacitor, 0603 Pkg.
C6, C8, C11, C14, C15	100 pF Capacitor, 0402 Pkg.
C12	3.6 pF Capacitor, 0402 Pkg.
C13	2.7 pF Capacitor, 0402 Pkg.
L1	18 nH Inductor, 0402 Pkg.
R1	130 Ohms Resistor, 0603 Pkg.
U1	HMC921LP4E Linear Amplifier
PCB [2]	130090 Evaluation PCB

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350 or Arlon 25FR

The circuit board used in this application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.

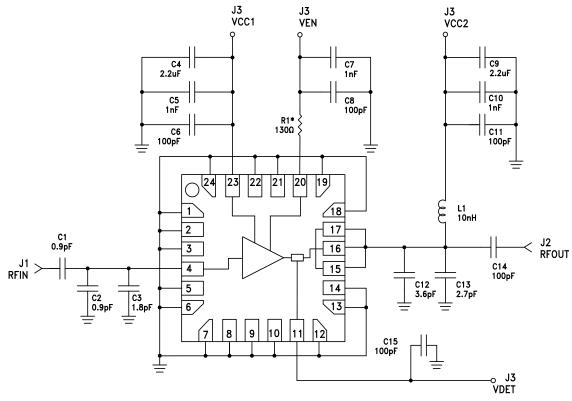




## GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz

### 1900 MHz Application Circuit

This circuit was used to specify the performance for 1800 - 2000 MHz operation. Contact the HMC Applications Group for assistance in optimizing performance for your application.



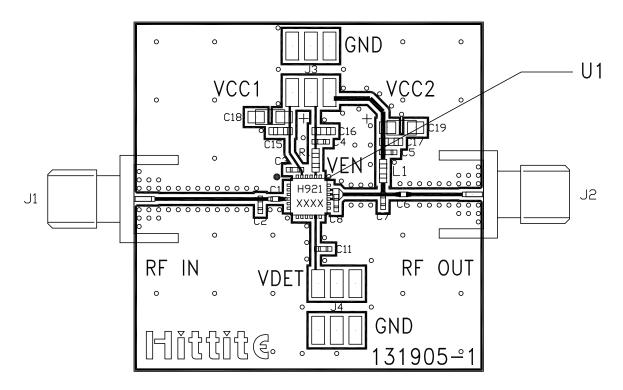
<sup>\*</sup> R1 = 130 Ohms for 700 mA bias, 270 Ohms for 400 mA bias.





### GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz

### 2150 MHz Evaluation PCB



### List of Materials for 2150 MHz Evaluation PCB 131924 [1]

Item	Description
J1, J2	SMA Connector
J3, J4	DC Pin
C1	3.9 pF Capacitor, 0402 Pkg.
C2, C8	4.3 pF Capacitor, 0402 Pkg.
C7	1.8 pF Capacitor, 0402 Pkg.
C3 - C6, C11	100 pF Capacitor, 0402 Pkg.
C15, C16, C17	1000 pF Capacitor, 0402 Pkg.
C18, C19	2.2 uF Capacitor, Case A.
R1	130 ohms Resistor, 0603 Pkg.
L1	10 nH Inductor, 0603 Pkg.
U1	HMC921LP4E Amplifier
PCB [2]	131905 Evaluation PCB

<sup>[1]</sup> Reference this number when ordering complete evaluation PCB

The circuit board used in this application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.

<sup>[2]</sup> Circuit Board Material: Rogers 4350 or Arlon 25 FR

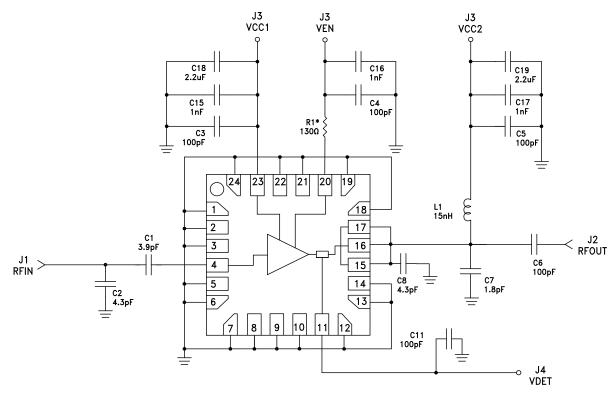




## GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz

### 2150 MHz Application Circuit

This circuit was used to specify the performance for 2000 - 2200 MHz operation. Contact the HMC Applications Group for assistance in optimizing performance for your application.



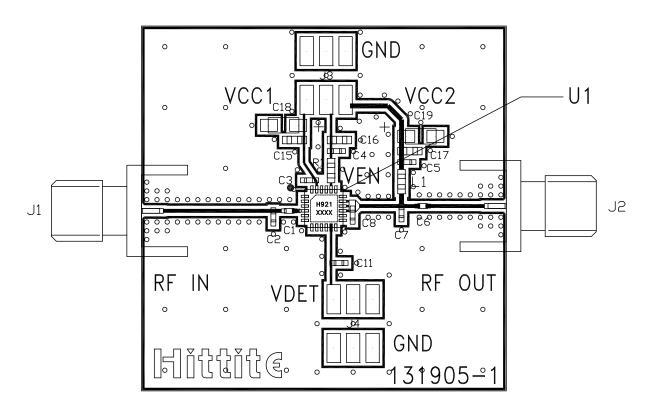
<sup>\*</sup> R1 = 130 Ohms for 700 mA bias, 270 Ohms for 400 mA bias.





## GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz

### 2700 MHz Evaluation PCB



### List of Materials for 2700 MHz Evaluation PCB 131907 [1]

Item	Description
J1, J2	SMA Connector
J3, J4	DC Pin
C1, C2	2.4 pF Capacitor, 0402 Pkg.
C7	1.3 pF Capacitor, 0402 Pkg.
C3 - C6, C11	100 pF Capacitor, 0402 Pkg.
C15, C16, C17	1000 pF Capacitor, 0402 Pkg.
C18, C19	2.2 uF Capacitor, Case A.
R1	130 ohms Resistor, 0603 Pkg.
L1	10 nH Inductor, 0603 Pkg.
U1	HMC921LP4E Amplifier
PCB [2]	131905 Evaluation PCB

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350 or Arlon 25 FR

The circuit board used in this application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.

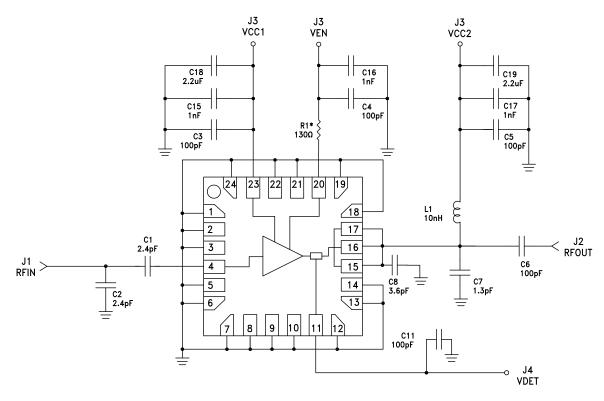




## GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz

### 2700 MHz Application Circuit

This circuit was used to specify the performance for 2500 - 2800 MHz operation. Contact the HMC Applications Group for assistance in optimizing performance for your application.



<sup>\*</sup> R1 = 130 Ohms for 700 mA bias, 270 Ohms for 400 mA bias.







**ANALOG**DEVICES

GaAs HBT MMIC 2 WATT POWER AMPLIFIER, 0.4 - 2.7 GHz

Notes: